





Frequency Tolerance/Stability ______ ±20ppm Maximum

Operating Temperature Range - 0°C to +70°C

TS -66.666M Nominal Frequency 66.666MHz

Pin 1 Connection
Tri-State (High Impedance)

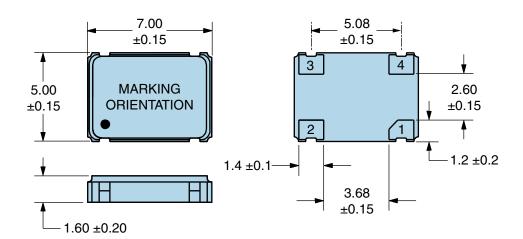
- Duty Cycle 50 ±10(%)

Operating 260°C Referred ing at 25°C ±5ppm/Y perating Temperature Range 0°C to +7 pply Voltage 1.8Vdc ± put Current 4mA Max atput Voltage Logic High (Voh) 90% of V atput Voltage Logic Low (Vol) 10% of V se/Fall Time 4nSec M tty Cycle 50 ±10(% ad Drive Capability 15pF Ma atput Logic Type CMOS	Maximum (Inclusive of all conditions: Calibration Tolerance at 25°C, Frequency Stability over the green Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, eflow, Shock, and Vibration) ear Maximum 0°C
Operating 260°C Referred ing at 25°C ±5ppm/Y perating Temperature Range 0°C to +7 pply Voltage 1.8Vdc ± put Current 4mA Max atput Voltage Logic High (Voh) 90% of V atput Voltage Logic Low (Vol) 10% of V perating Temperature Range 0°C to +7 and Max atput Voltage Logic High (Voh) 90% of V atput Voltage Logic Low (Vol) 10% of V perating Temperature Range 0°C to +7 and Max atput Voltage Logic High (Voh) 90% of V atput Voltage Logic Low (Vol) 10% of V atput Voltage So ±10(% ad Drive Capability 15pF Ma atput Logic Type CMOS	g Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at 25°, bflow, Shock, and Vibration) ear Maximum 10°C 5% timum (No Load) dd Minimum (IOH = -8mA)
perating Temperature Range 0°C to +7 pply Voltage 1.8Vdc ± but Current 4mA Max tiput Voltage Logic High (Voh) 10% of V tiput Voltage Logic Low (Vol) 10% of V tiput Voltage Logic Low (Vol) 5e/Fall Time 4nSec M ty Cycle 50 ±10(% ad Drive Capability 15pF Ma tiput Logic Type CMOS	0°C 5% imum (No Load) dd Minimum (IOH = -8mA)
pply Voltage 1.8Vdc ± but Current 4mA Max stput Voltage Logic High (Voh) 90% of V se/Fall Time 4nSec M tty Cycle 50 ±10(% ad Drive Capability 15pF Ma stput Logic Type 1.8Vdc ± 4mA Max 4mSec M 50 ±0 V 60 Max 4mSec M 60 Max 6	55% imum (No Load) dd Minimum (IOH = -8mA)
Amage	imum (No Load) dd Minimum (IOH = -8mA)
ttput Voltage Logic High (Voh) 10% of Voltage Logic Low (Vol) 10% of Voltage Logic Low (Vol) 4nSec M 4nSec M 50 ±10(% ad Drive Capability 15pF Ma ttput Logic Type CMOS	dd Minimum (IOH = -8mA)
tetput Voltage Logic Low (Vol) 10% of V se/Fall Time 4nSec M ty Cycle 50 ±10(% ad Drive Capability 15pF Ma tetput Logic Type CMOS	
se/Fall Time 4nSec M ty Cycle 50 ±10 (% ad Drive Capability 15pF Ma ttput Logic Type CMOS	dd Maximum (IOL = +8mA)
ty Cycle 50 ±10(% ad Drive Capability 15pF Ma tput Logic Type CMOS	
ad Drive Capability 15pF Ma tput Logic Type CMOS	aximum (Measured at 20% to 80% of waveform)
tput Logic Type CMOS) (Measured at 50% of waveform)
	ximum
1 Connection Tri-State	
	(High Impedance)
-State Input Voltage (Vih and Vil) 90% of V Impedant	dd Minimum or No Connect to Enable Output, 10% of Vdd Maximum to Disable Output (High ce)
andby Current 10µA Ma	ximum (Pin 1 = Ground)
solute Clock Jitter ±100pSe	c Maximum
art Up Time 10mSec	Maximum
orage Temperature Range -55°C to	WAAIIIUIII

ENVIRONMENTAL & MECHANICAL SPECIFICATIONS		
ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V	
Fine Leak Test	MIL-STD-883, Method 1014, Condition A	
Flammability	UL94-V0	
Gross Leak Test	MIL-STD-883, Method 1014, Condition C	
Mechanical Shock	MIL-STD-883, Method 2002, Condition B	
Moisture Resistance	MIL-STD-883, Method 1004	
Moisture Sensitivity	J-STD-020, MSL 1	
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K	
Resistance to Solvents	MIL-STD-202, Method 215	
Solderability	MIL-STD-883, Method 2003	
Temperature Cycling	MIL-STD-883, Method 1010, Condition B	
Vibration	MIL-STD-883, Method 2007, Condition A	



MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Case Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	66.666M
3	XXXXXX XXXXXX=Ecliptek Manufacturing Identifier

Suggested Solder Pad Layout

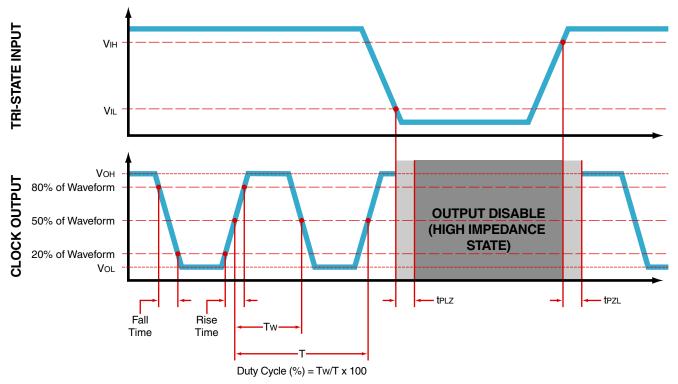
All Dimensions in Millimeters



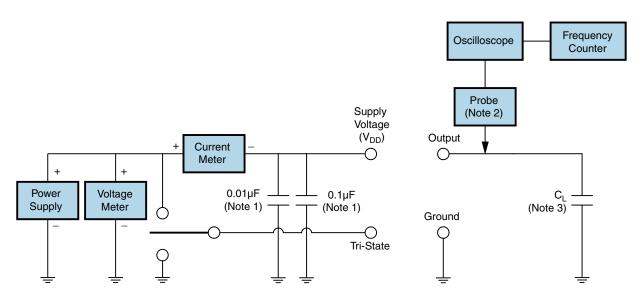
All Tolerances are ±0.1



OUTPUT WAVEFORM & TIMING DIAGRAM



Test Circuit for CMOS Output



- Note 1: An external 0.01µF ceramic bypass capacitor in parallel with a 0.1µF high frequency ceramic bypass capacitor close (less than 2mm) to the package ground and supply voltage pin is required.
- Note 2: A low capacitance (<12pF), 10X attenuation factor, high impedance (>10Mohms), and high bandwidth (>300MHz) passive probe is recommended.
- Note 3: Capacitance value C₁ includes sum of all probe and fixture capacitance.



Recommended Solder Reflow Methods



High Temperature Infrared/Convection

<u> </u>	
T _s MAX to T _∟ (Ramp-up Rate)	3°C/second Maximum
Preheat	
- Temperature Minimum (T _S MIN)	150°C
- Temperature Typical (T _s TYP)	175°C
- Temperature Maximum (T _s MAX)	200°C
- Time (t _s MIN)	60 - 180 Seconds
Ramp-up Rate (T _L to T _P)	3°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	217°C
- Time (t∟)	60 - 150 Seconds
Peak Temperature (T _P)	260°C Maximum for 10 Seconds Maximum
Target Peak Temperature (T _P Target)	250°C +0/-5°C
Time within 5°C of actual peak (tp)	20 - 40 seconds
Ramp-down Rate	6°C/second Maximum
Time 25°C to Peak Temperature (t)	8 minutes Maximum
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.



Recommended Solder Reflow Methods



Low Temperature Infrared/Convection 240°C

T _S MAX to T _L (Ramp-up Rate)	5°C/second Maximum
Preheat	
- Temperature Minimum (T _s MIN)	N/A
- Temperature Typical (T _S TYP)	150°C
- Temperature Maximum (T _s MAX)	N/A
- Time (t _s MIN)	60 - 120 Seconds
Ramp-up Rate (T _L to T _P)	5°C/second Maximum
Time Maintained Above:	
- Temperature (T∟)	150°C
- Time (t∟)	200 Seconds Maximum
Peak Temperature (T _P)	240°C Maximum
Target Peak Temperature (T _P Target)	240°C Maximum 1 Time / 230°C Maximum 2 Times
Time within 5°C of actual peak (tp)	10 seconds Maximum 2 Times / 80 seconds Maximum 1 Time
Ramp-down Rate	5°C/second Maximum
Time 25°C to Peak Temperature (t)	N/A
Moisture Sensitivity Level	Level 1
Additional Notes	Temperatures shown are applied to body of device.

Low Temperature Manual Soldering

185°C Maximum for 10 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

High Temperature Manual Soldering

260°C Maximum for 5 seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)